

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number:	PMN23UN,165
Manufacturer:	NXP USA Inc.
Package:	Please confirm with sales
Availability:	Please confirm with sales

Product Page:

<https://antrexco.com/product/details/nxp-usa-inc/pmn23un-165.html>

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Contact Information

Email: info@antrexco.com

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Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

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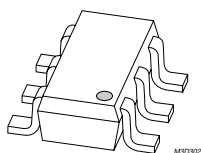
Should be replaced with:

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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia



PMN23UN

μTrenchMOS™ ultra low level FET

Rev. 01 — 16 June 2004

Product data

1. Product profile

1.1 Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

1.2 Features

- TrenchMOS™ technology
- Very fast switching
- Low threshold voltage
- Surface mounted package.

1.3 Applications

- Battery powered motor control
- High-speed switch in set top box power supplies
- Load switch in notebook computers
- Driver FET in DC-to-DC converters.

1.4 Quick reference data

- $V_{DS} \leq 20 \text{ V}$
- $P_{tot} \leq 1.75 \text{ W}$
- $I_D \leq 6.3 \text{ A}$
- $R_{DS(on)} \leq 28 \text{ m}\Omega$.

2. Pinning information

Table 1: Pinning - SOT457 (TSOP6), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1,2,5,6	drain (d)	Top view MBK092	mbb076
3	gate (g)		
4	source (s)		

SOT457 (TSOP6)



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3. Ordering information

Table 2: Ordering information

Type number	Package		Version
	Name	Description	
PMN23UN	TSOP6	Plastic surface mounted package; 6 leads	SOT457

4. Limiting values

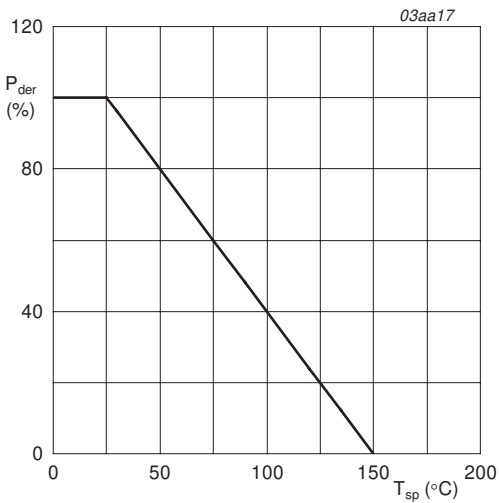
Table 3: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	20	V
V_{GS}	gate-source voltage (DC)		-	± 8	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}$; $V_{GS} = 4.5\text{ V}$; Figure 2 and 3	-	6.3	A
		$T_{sp} = 70\text{ °C}$; $V_{GS} = 4.5\text{ V}$; Figure 2	-	5	A
I_{DM}	peak drain current	$T_{sp} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Figure 3	-	25.2	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C}$; Figure 1	-	1.75	W
T_{stg}	storage temperature		-55	+150	°C
T_j	junction temperature		-55	+150	°C

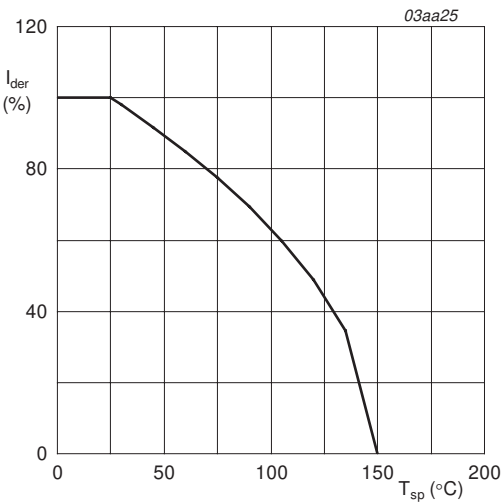
Source-drain diode

I_S	source (diode forward) current (DC)	$T_{sp} = 25\text{ °C}$	-	1.45	A
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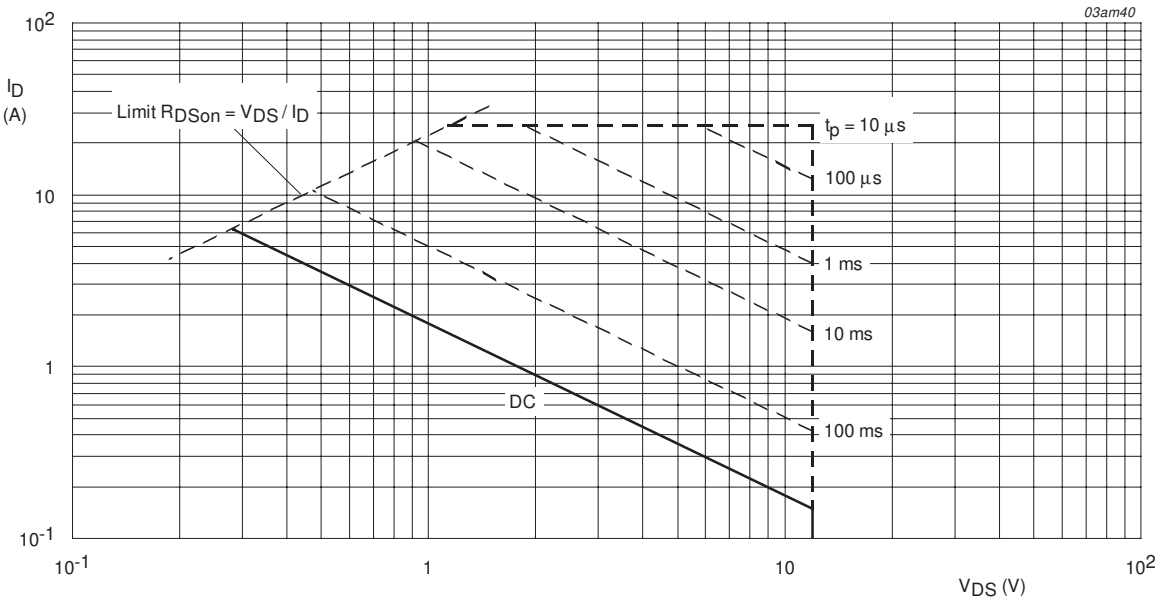
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature.



T_{sp} = 25 °C; I_{DM} is single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

5. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	Figure 4	-	-	70	K/W

5.1 Transient thermal impedance

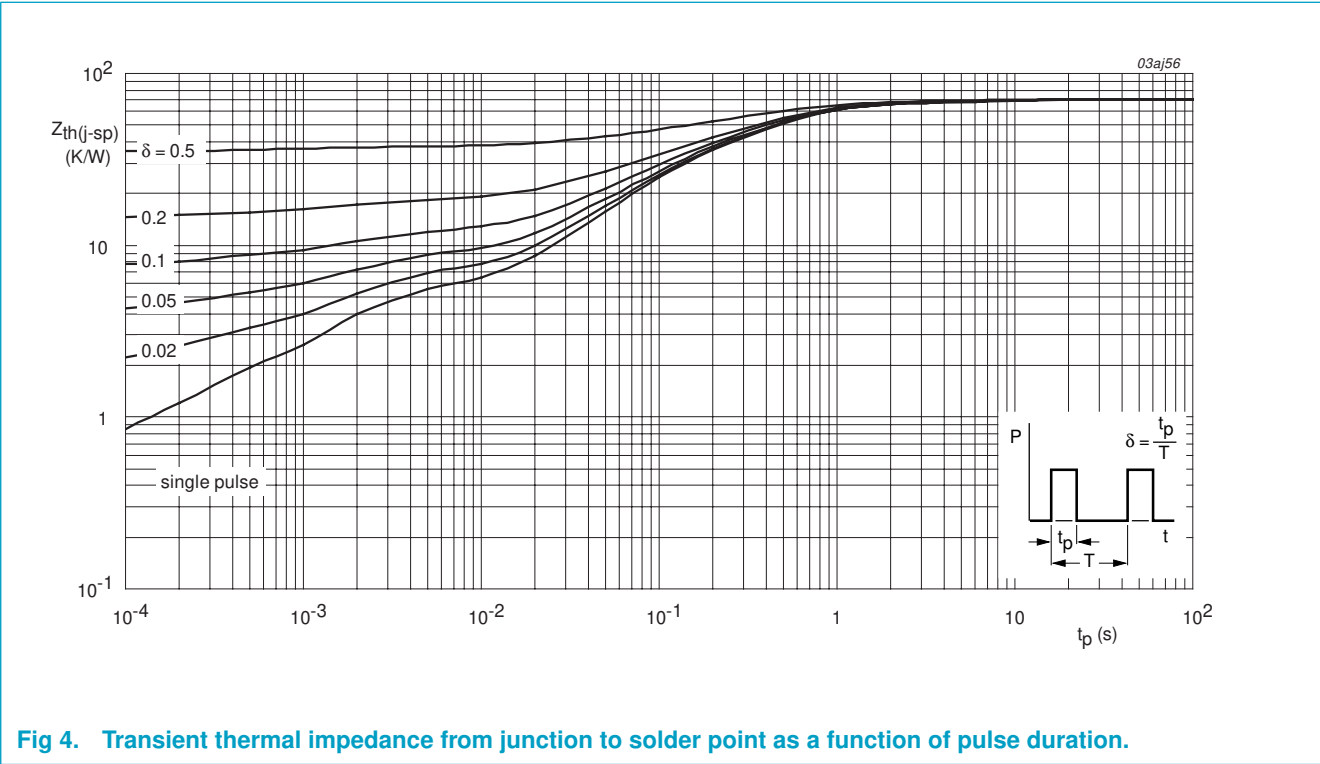


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration.

6. Characteristics

Table 5: Characteristics

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V	20	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; Figure 9 and 10	0.4	0.7	-	V
I _{DSS}	drain-source leakage current	V _{DS} = 16 V; V _{GS} = 0 V				
		T _j = 25 °C	-	0.01	1.0	μA
		T _j = 55 °C	-	-	10	μA
I _{GSS}	gate-source leakage current	V _{GS} = ±8 V; V _{DS} = 0 V	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 4.5 V; I _D = 2 A; Figure 7 and 8	-	23	28	mΩ
		V _{GS} = 2.5 V; I _D = 2 A; Figure 7 and 8	-	29	34.4	mΩ
		V _{GS} = 1.8 V; I _D = 1.5 A; Figure 7 and 8	-	37	52	mΩ
Dynamic characteristics						
Q _{g(tot)}	total gate charge	V _{DD} = 10 V; V _{GS} = 4.5 V; I _D = 3.8 A; Figure 13	-	10.6	-	nC
Q _{gs}	gate-source charge		-	1.8	-	nC
Q _{gd}	gate-drain (Miller) charge		-	2.1	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 10 V; f = 1 MHz; Figure 11	-	740	-	pF
C _{oss}	output capacitance		-	185	-	pF
C _{rss}	reverse transfer capacitance		-	125	-	pF
t _{d(on)}	turn-on delay time	V _{DD} = 10 V; R _L = 10 Ω; V _{GS} = 4.5 V; R _G = 6 Ω	-	8.5	-	ns
t _r	rise time		-	14.5	-	ns
t _{d(off)}	turn-off delay time		-	55	-	ns
t _f	fall time		-	16	-	ns
Source-drain diode						
V _{SD}	source-drain (diode forward) voltage	I _S = 1.7 A; V _{GS} = 0 V; Figure 12	-	0.8	1.2	V

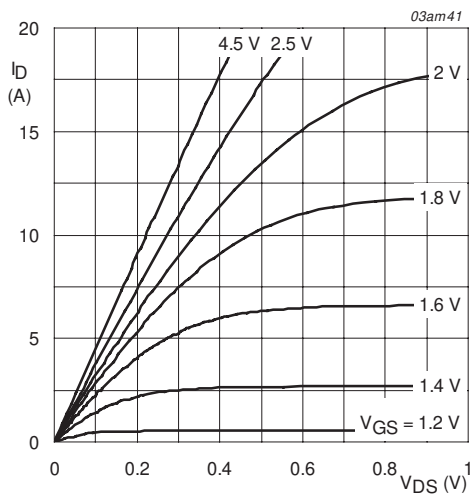


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.

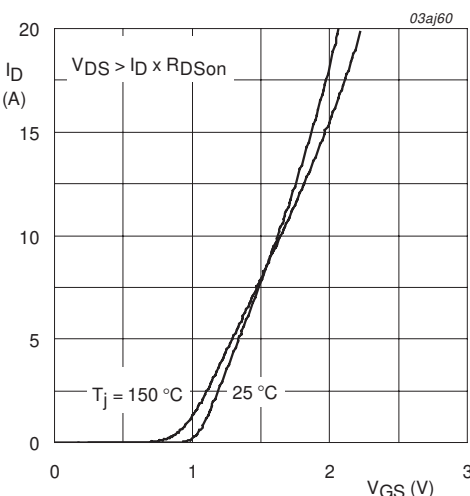


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.

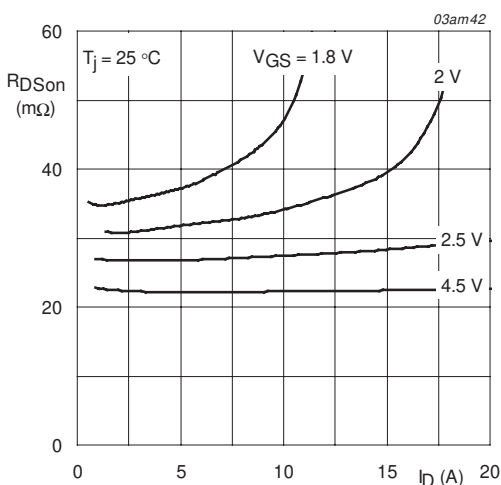


Fig 7. Drain-source on-state resistance as a function of drain current; typical values.

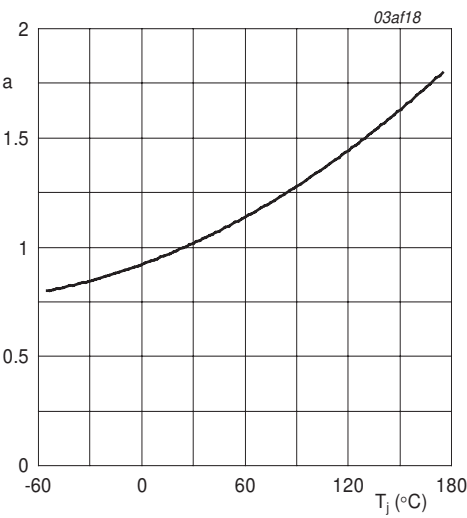
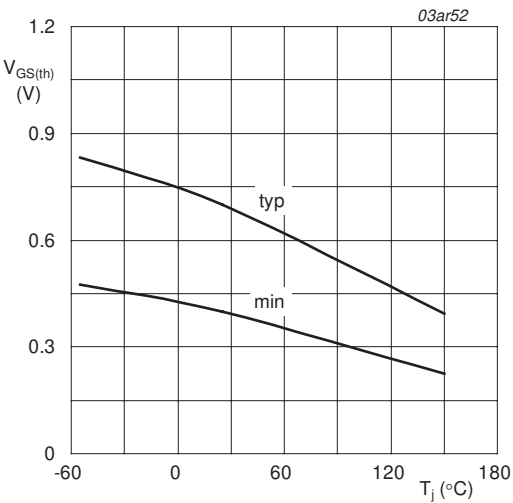
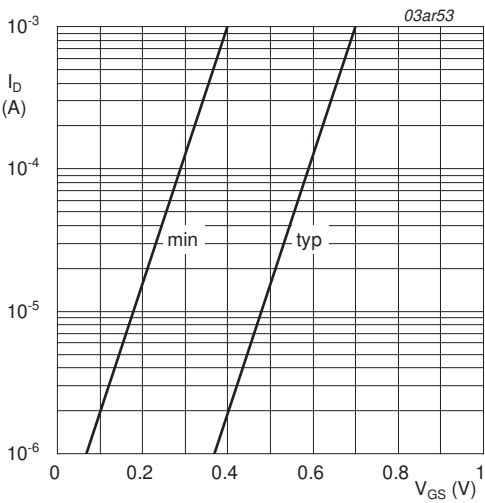


Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



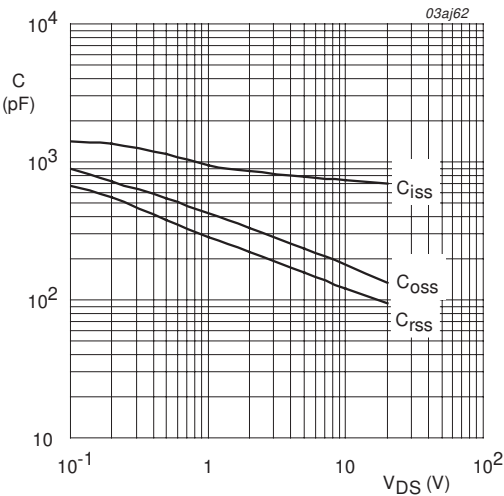
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



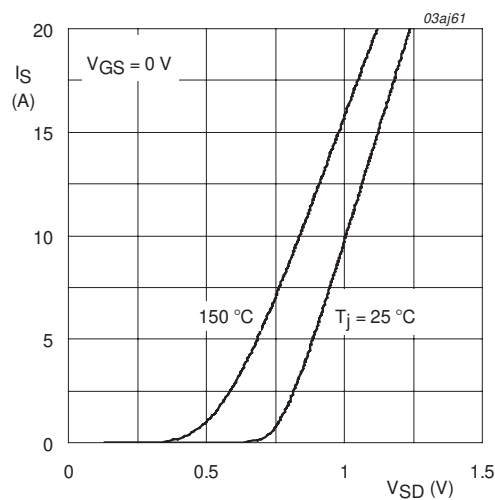
$T_j = 25 \text{ °C}; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



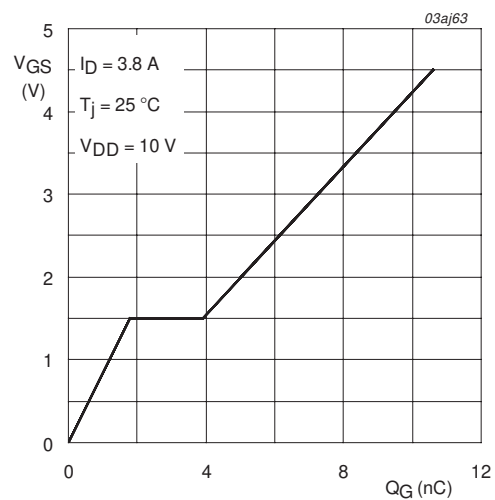
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25$ °C and 150 °C; $V_{GS} = 0$ V

Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 3.8$ A; $V_{DD} = 10$ V

Fig 13. Gate-source voltage as a function of gate charge; typical values.

7. Package outline

Plastic surface mounted package; 6 leads

SOT457

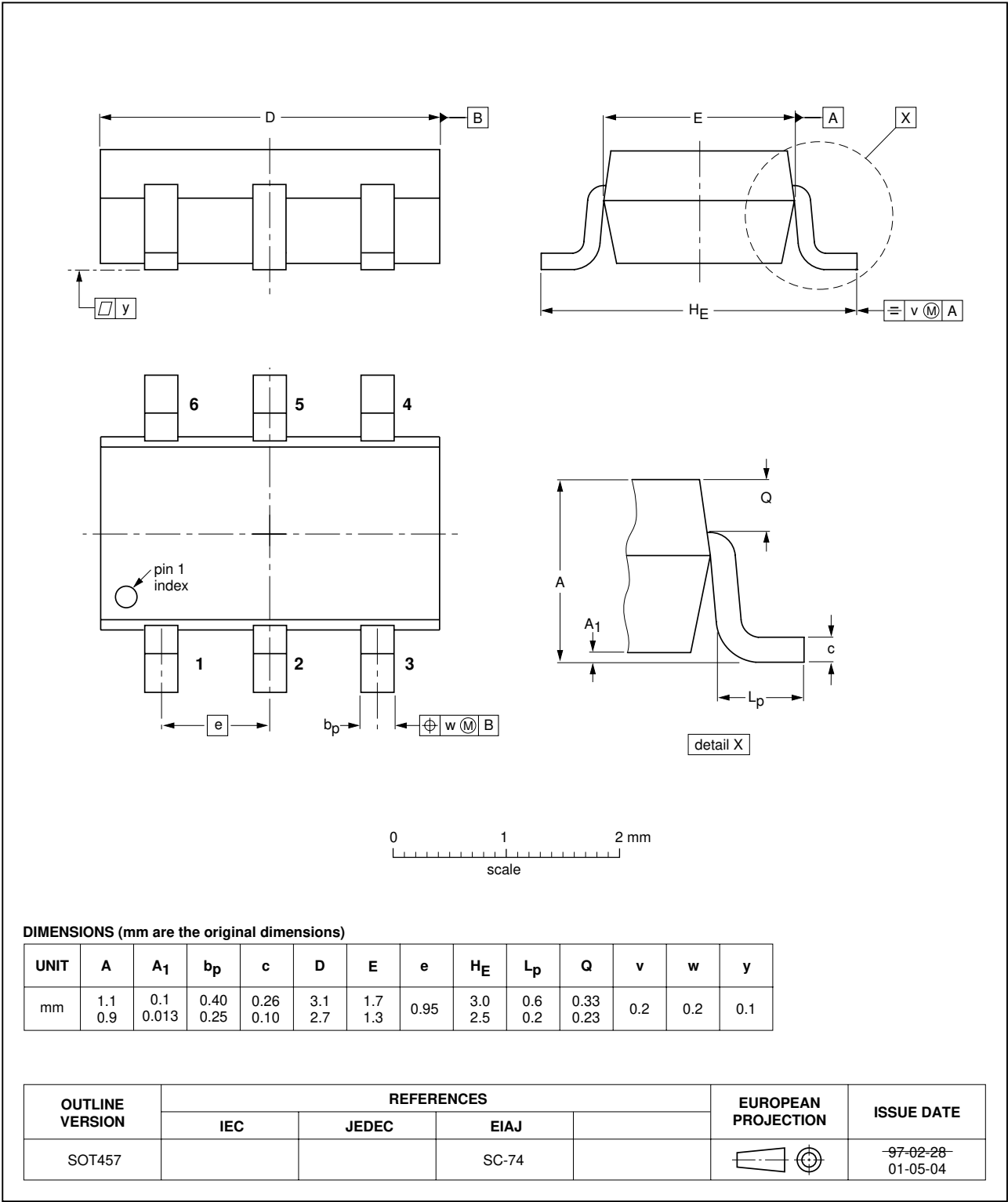


Fig 14. SOT457 (TSOP6).

8. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
01	20040616	-	Product data (9397 750 13351)

9. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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For additional information, please visit <http://www.semiconductors.philips.com>.

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Fax: +31 40 27 24825

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